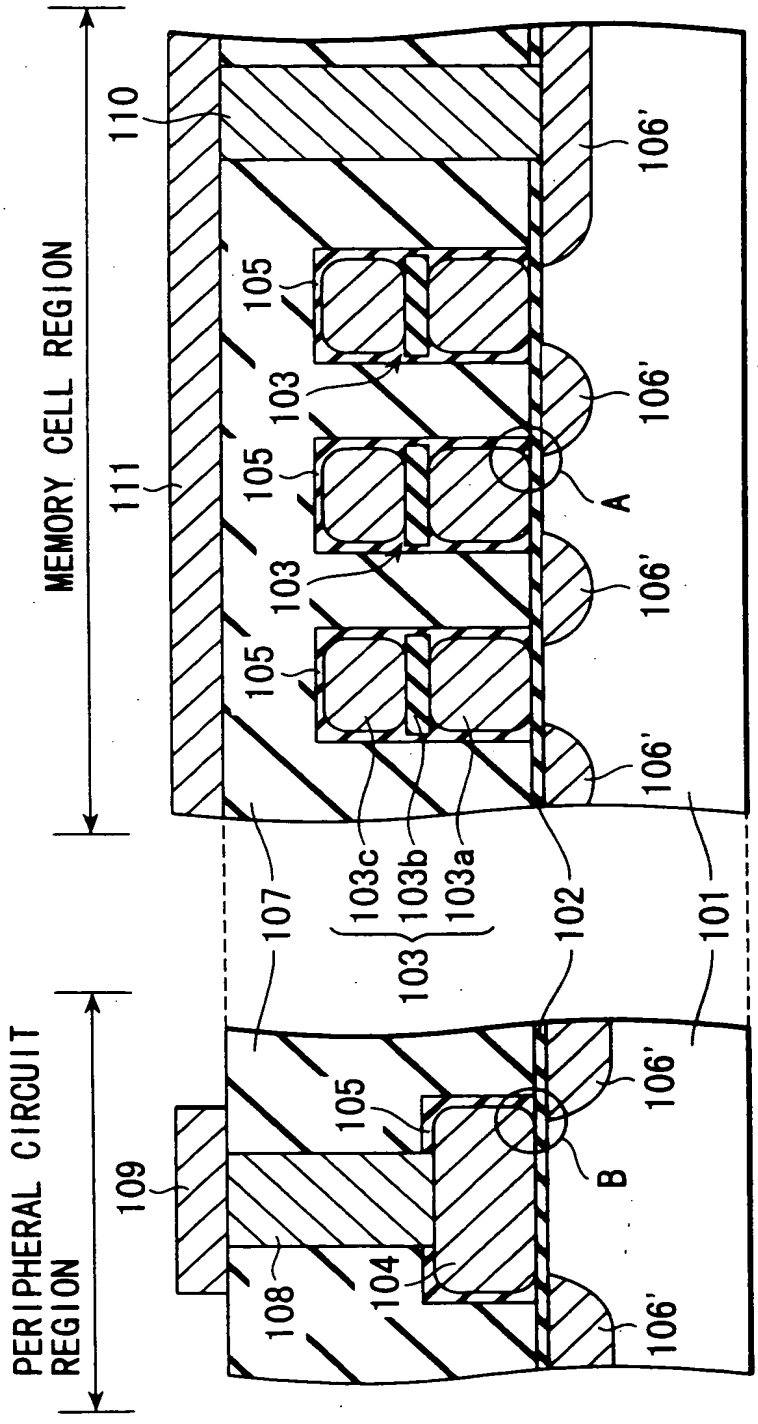


FIG. 1
PRIOR ART

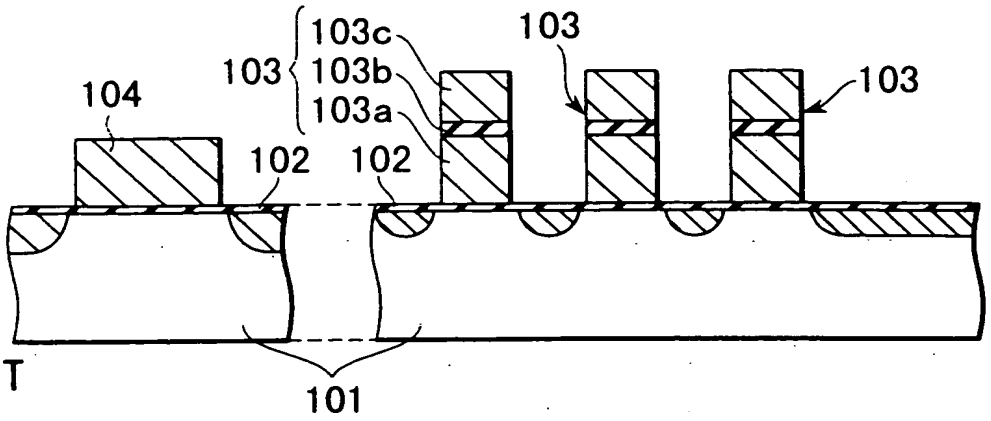


FIG. 2A
PRIOR ART

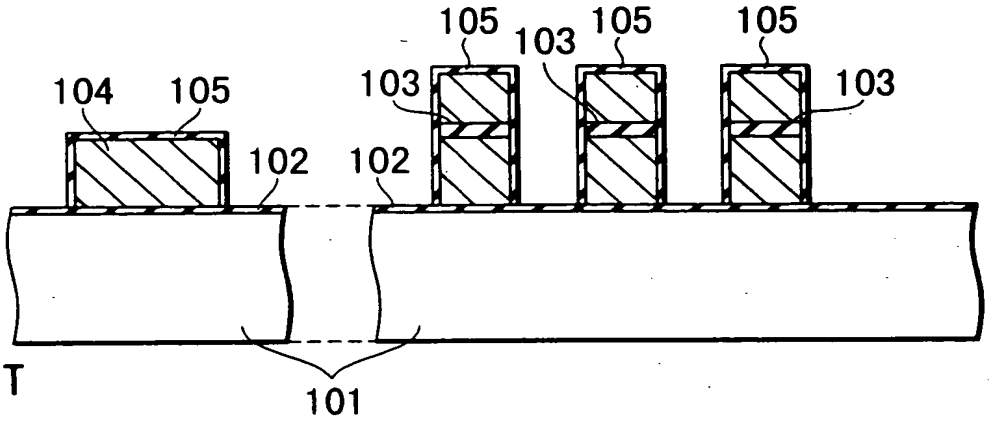


FIG. 2B
PRIOR ART

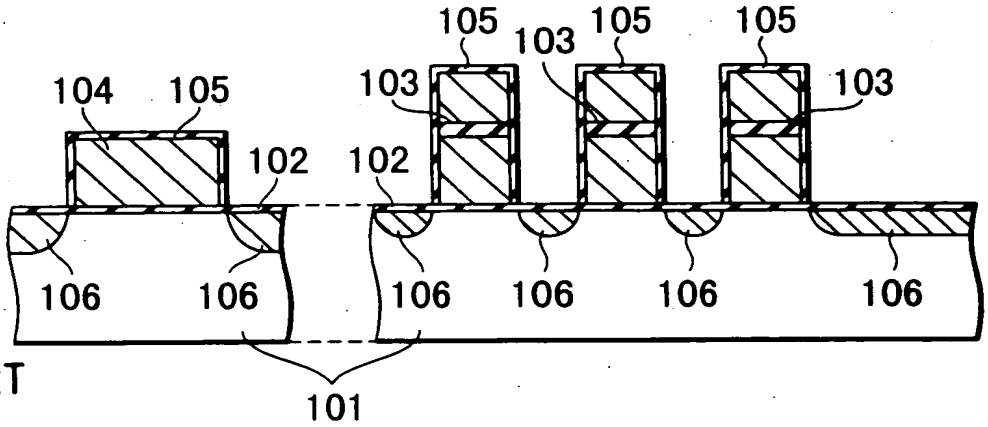


FIG. 2C
PRIOR ART

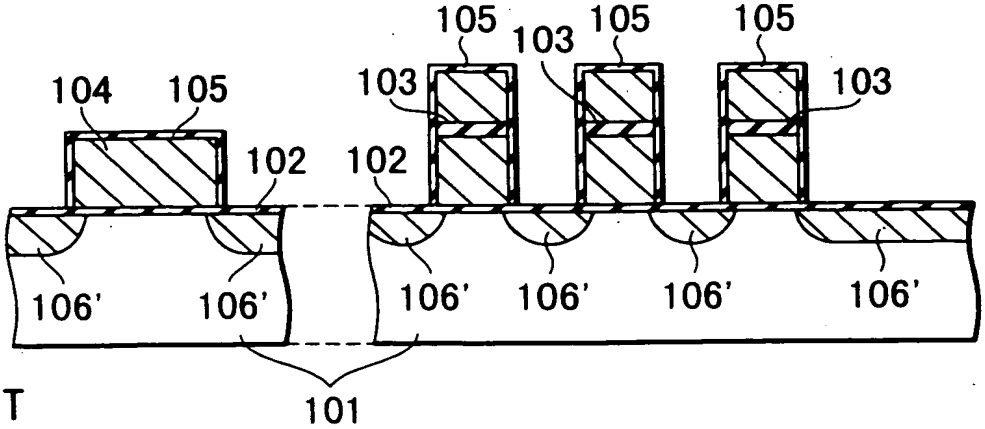


FIG. 2D
PRIOR ART

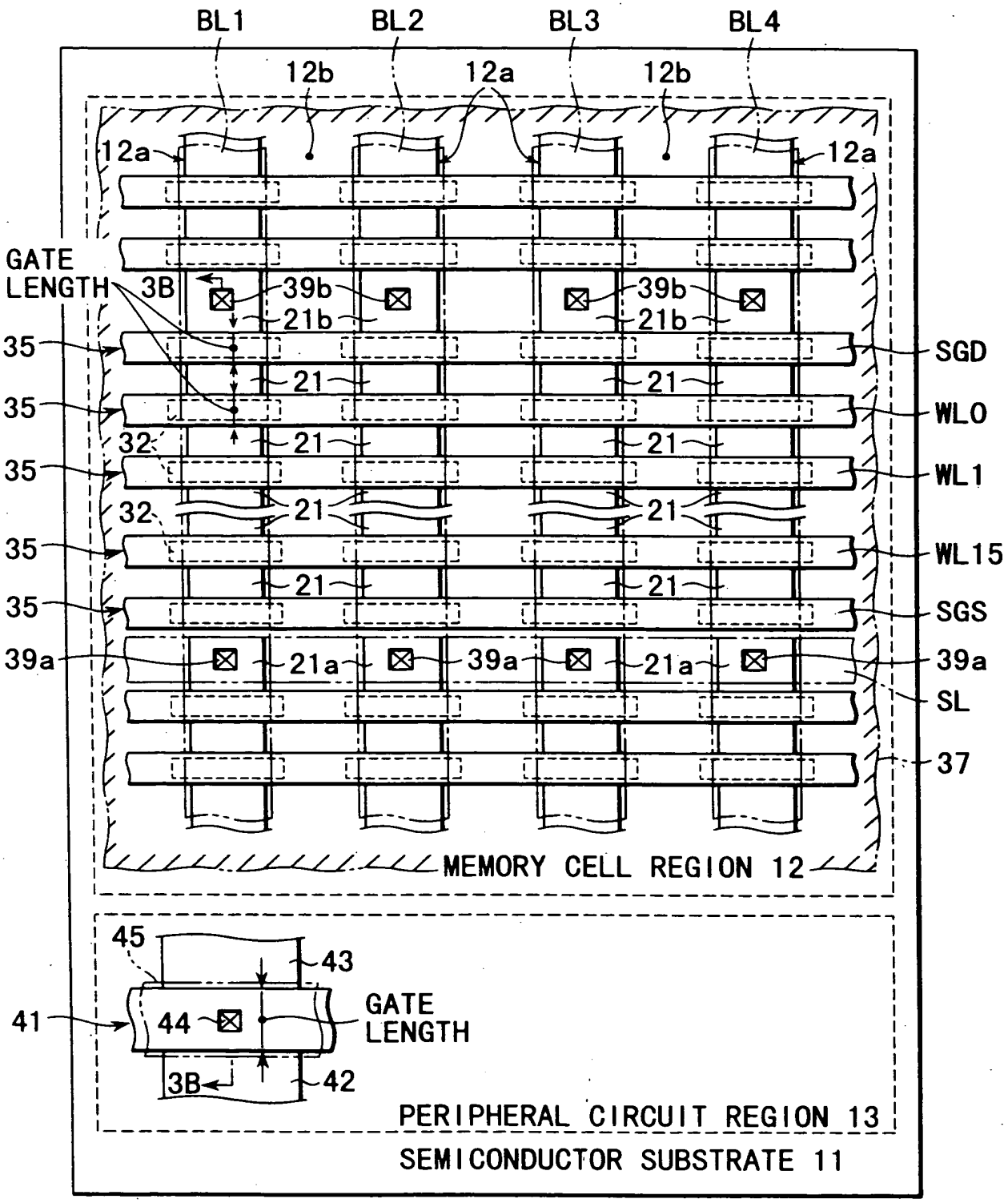

BL1
BL2
BL3
BL4
12b
12a
12b
12a
12a
GATE LENGTH
3B
39b
21b
39b
21b
35
SGD
21
21
35
WL0
32
21
21
35
WL1
32
21
21
35
WL15
21
21
35
SGS
39a
21a
39a
21a
39a
SL
37
MEMORY CELL REGION 12
45
43
41
44
GATE LENGTH
3B
42
PERIPHERAL CIRCUIT REGION 13
SEMICONDUCTOR SUBSTRATE 11

FIG. 3A

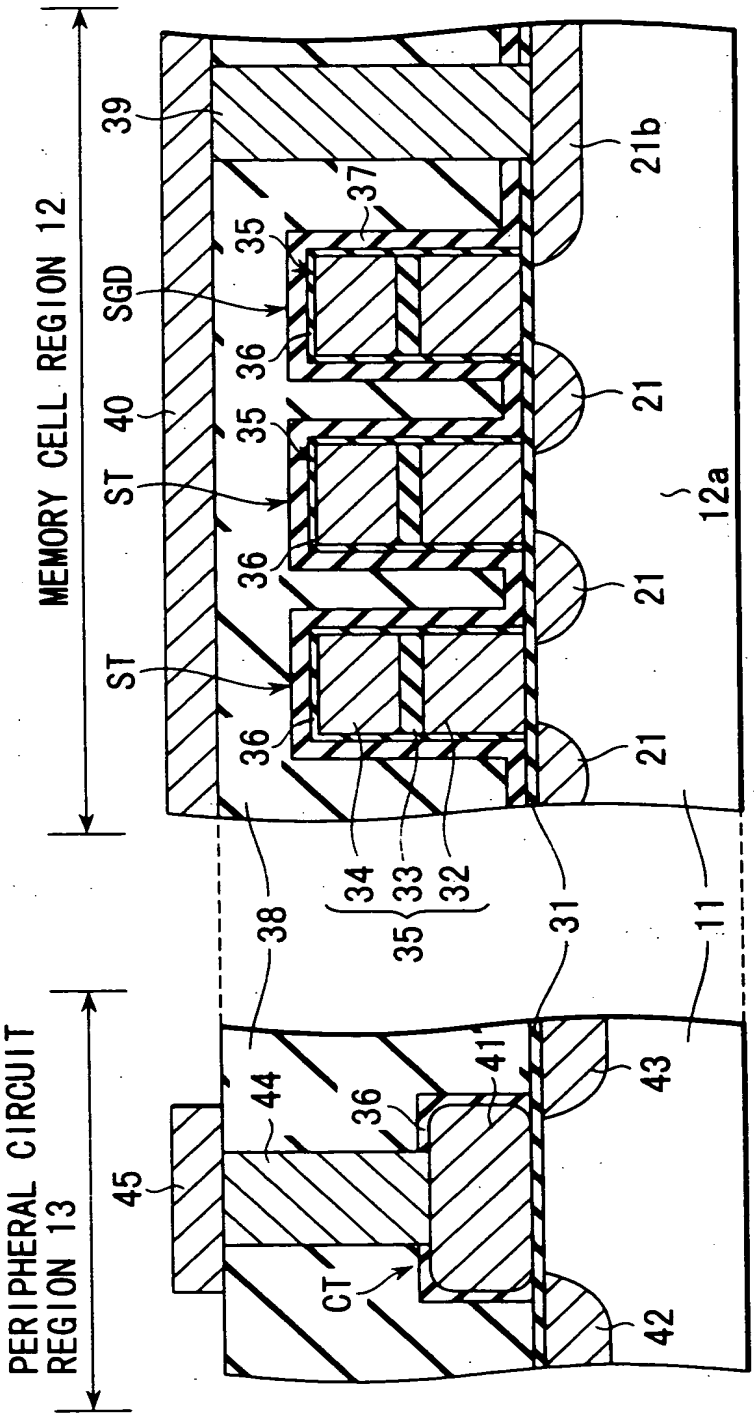

MEMORY CELL REGION 12
PERIPHERAL CIRCUIT REGION 13
39
37
35
SGD
36
40
ST
21b
21
12a
45
44
41
43
CT
42
38
34
33
32
31
11

FIG. 3B

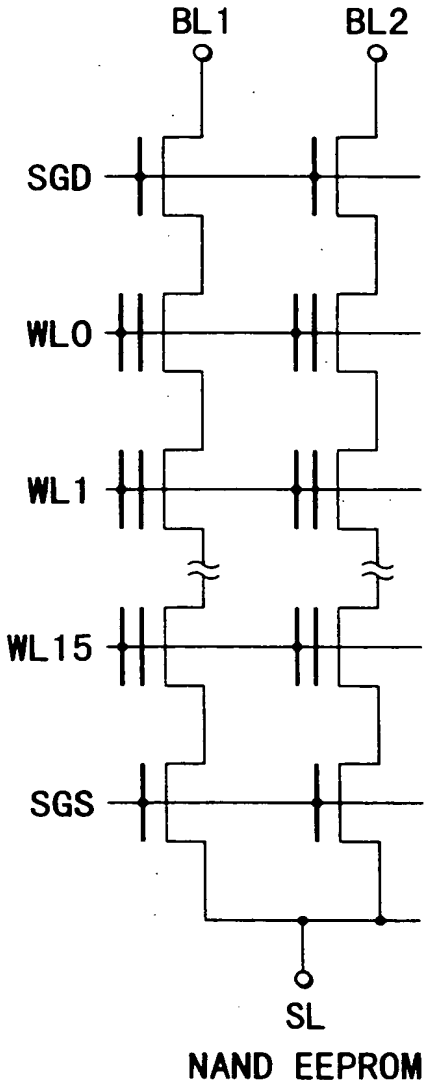


FIG. 4

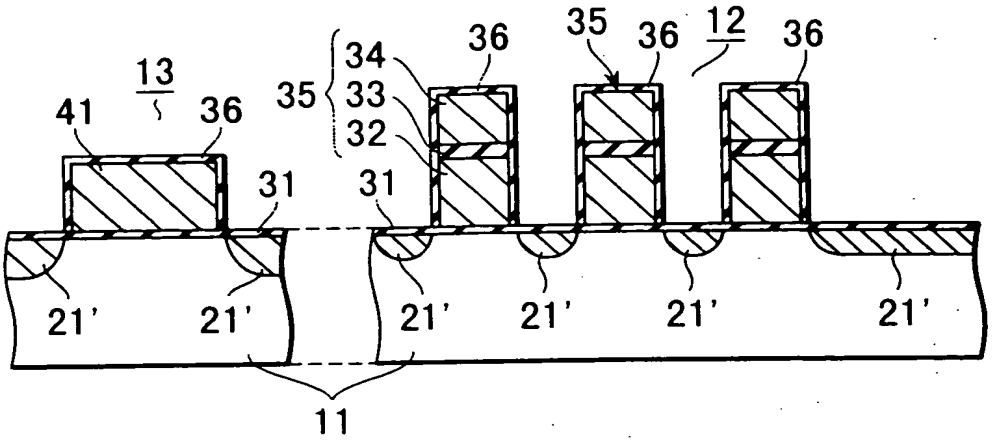


FIG. 5A

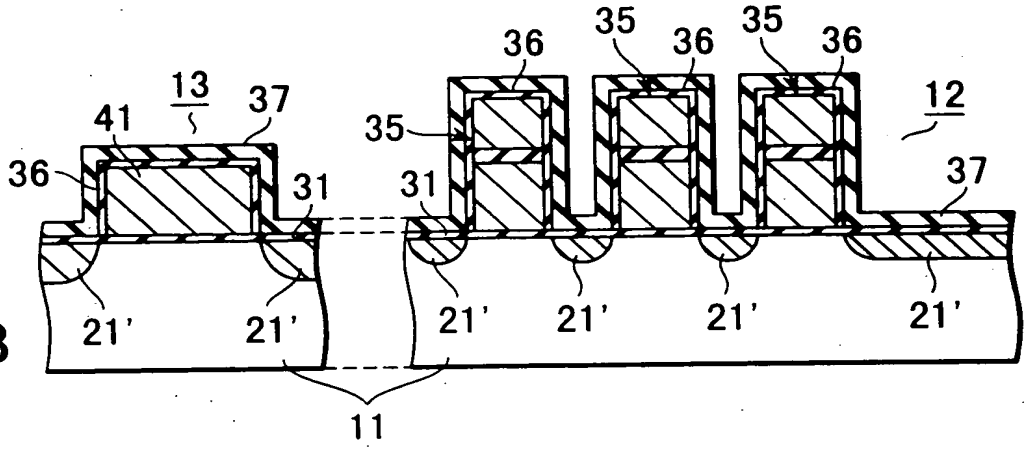


FIG. 5B

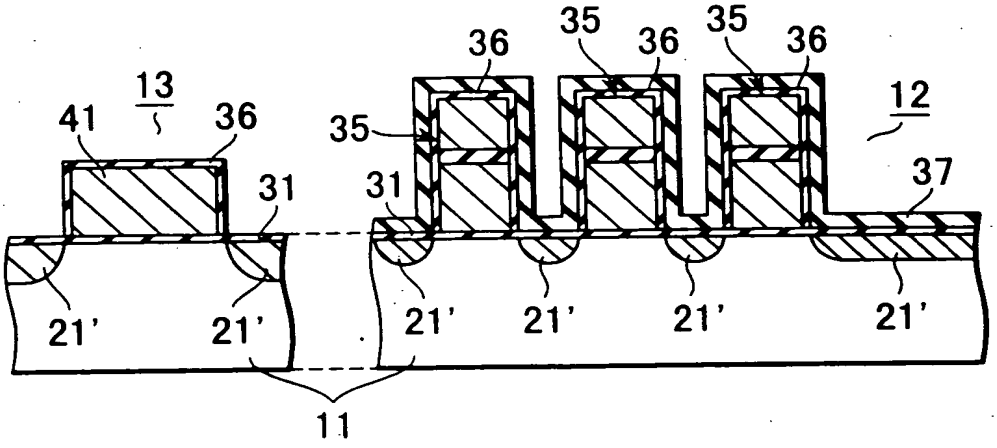


FIG. 5C

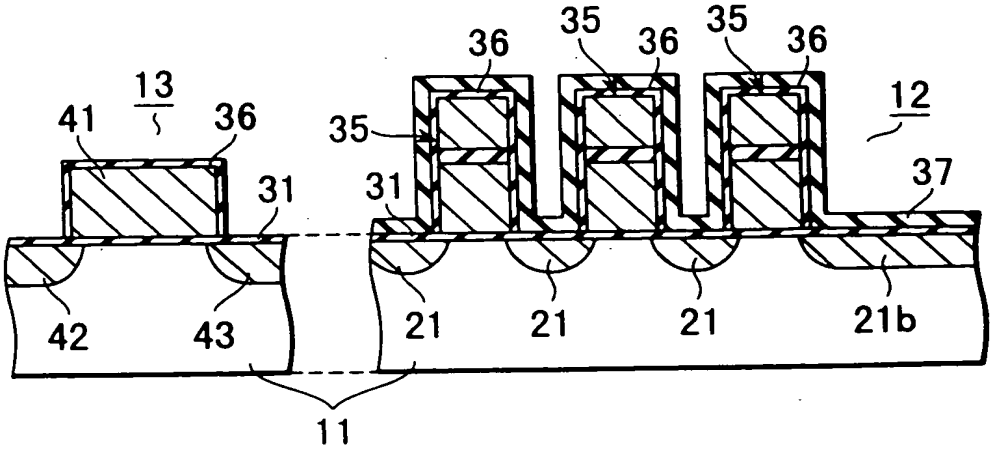


FIG. 5D

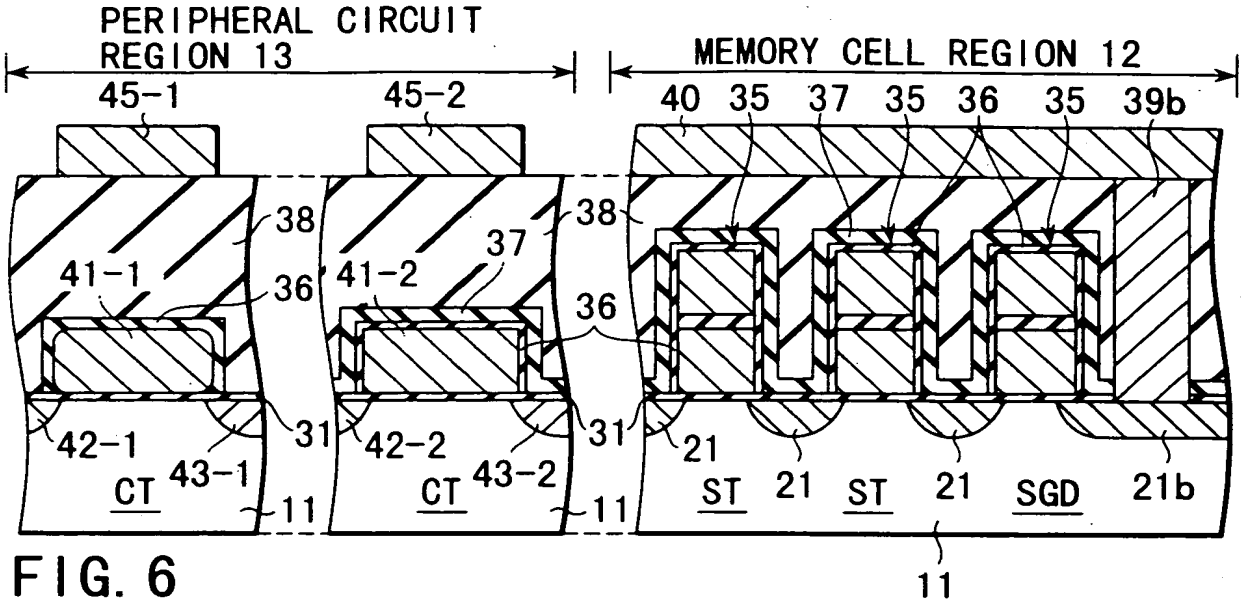


FIG. 6

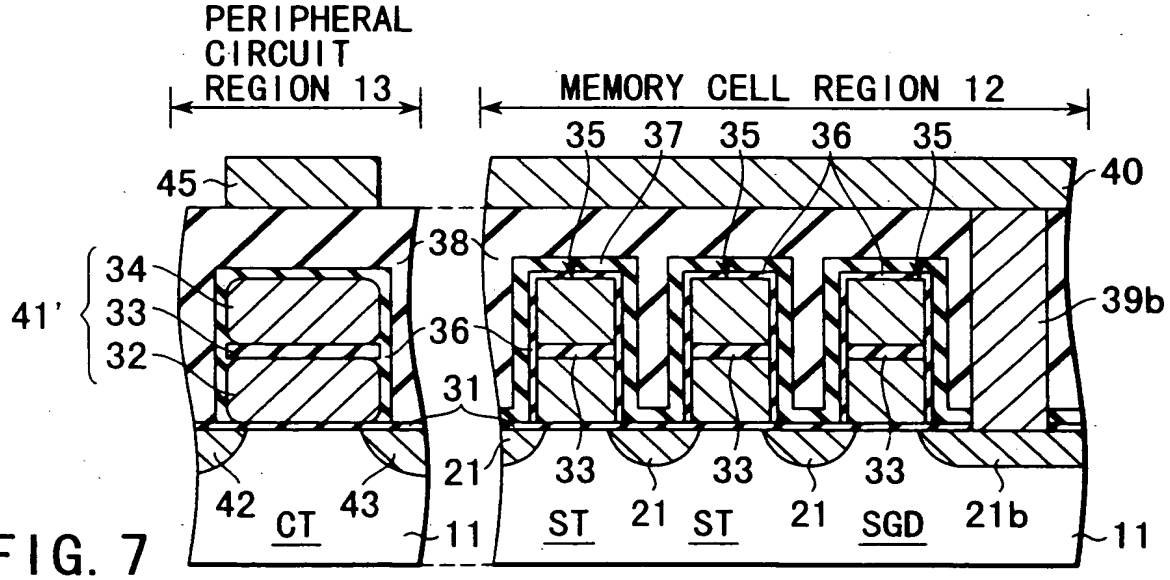


FIG. 7

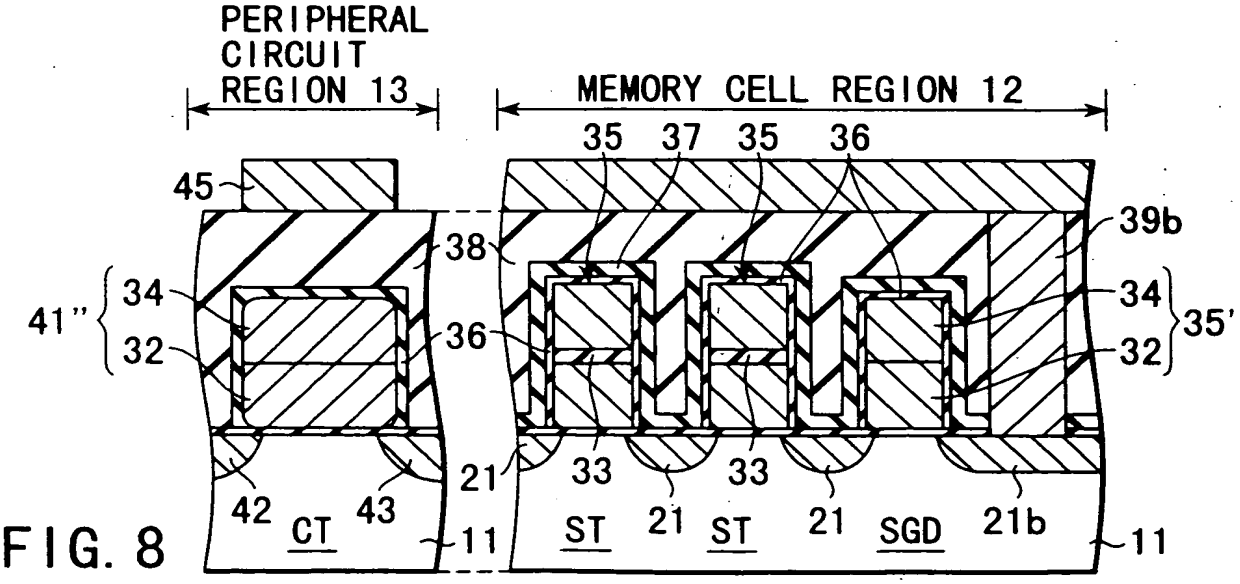


FIG. 8

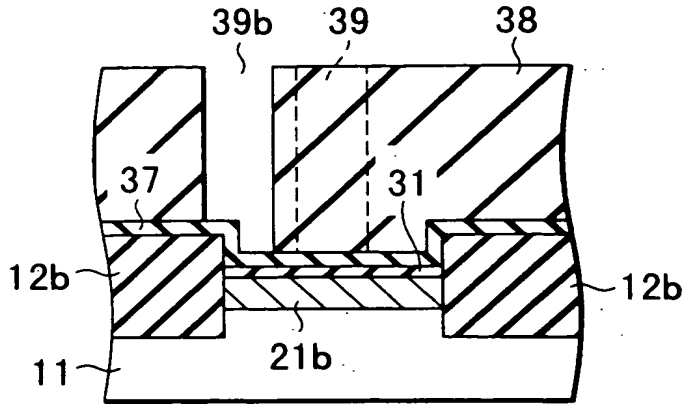


FIG. 9A

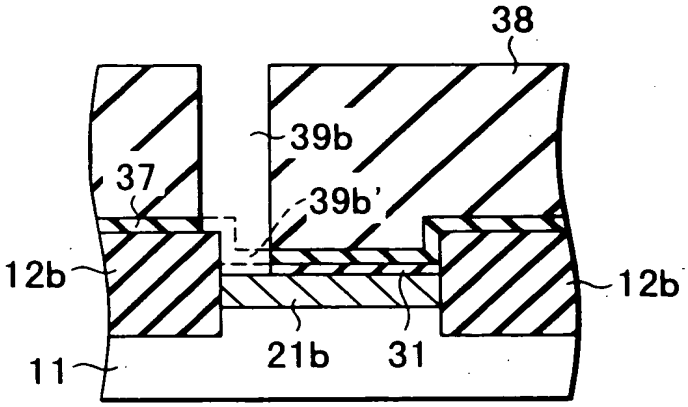


FIG. 9B

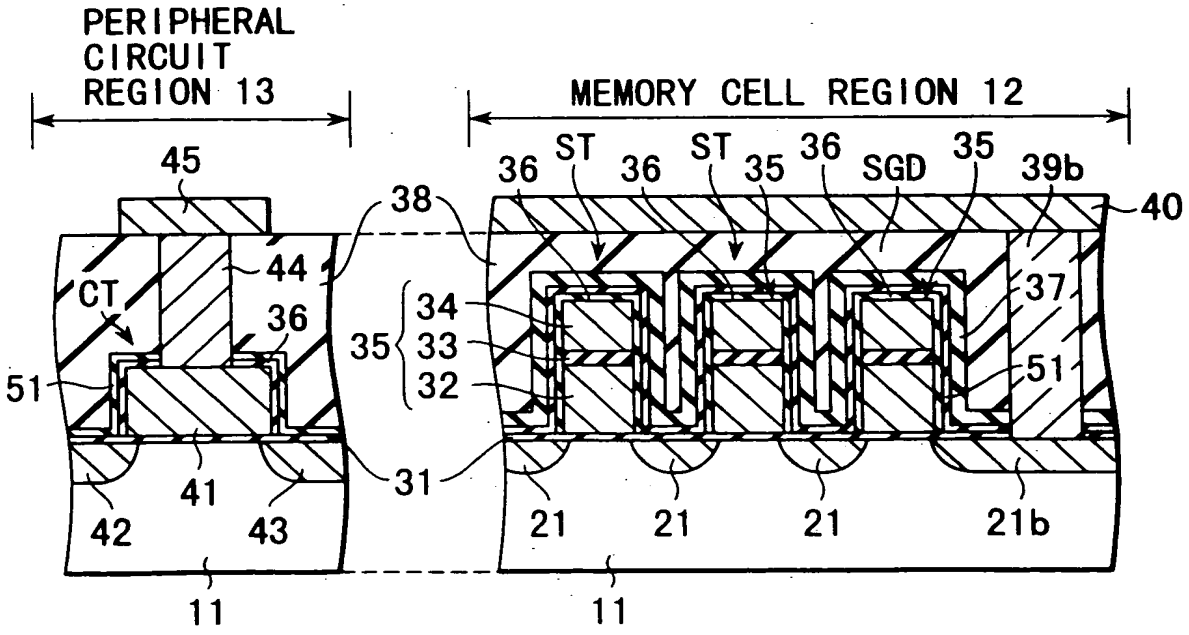


FIG. 12

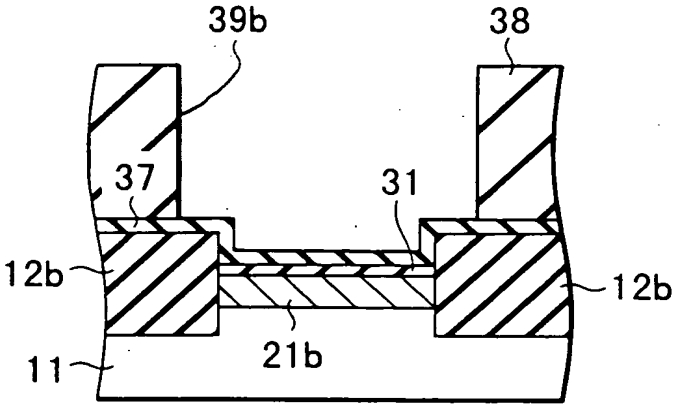


FIG. 10A

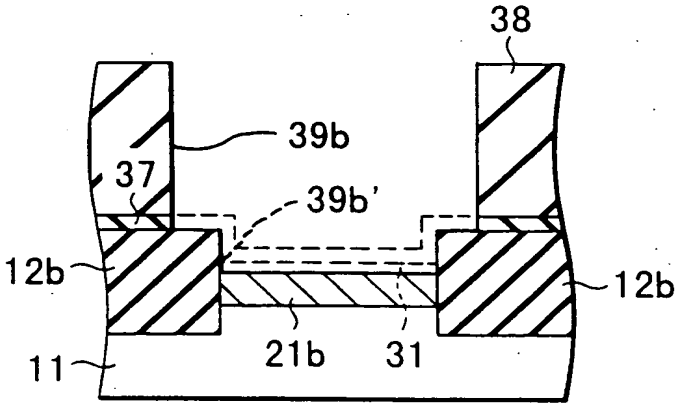


FIG. 10B

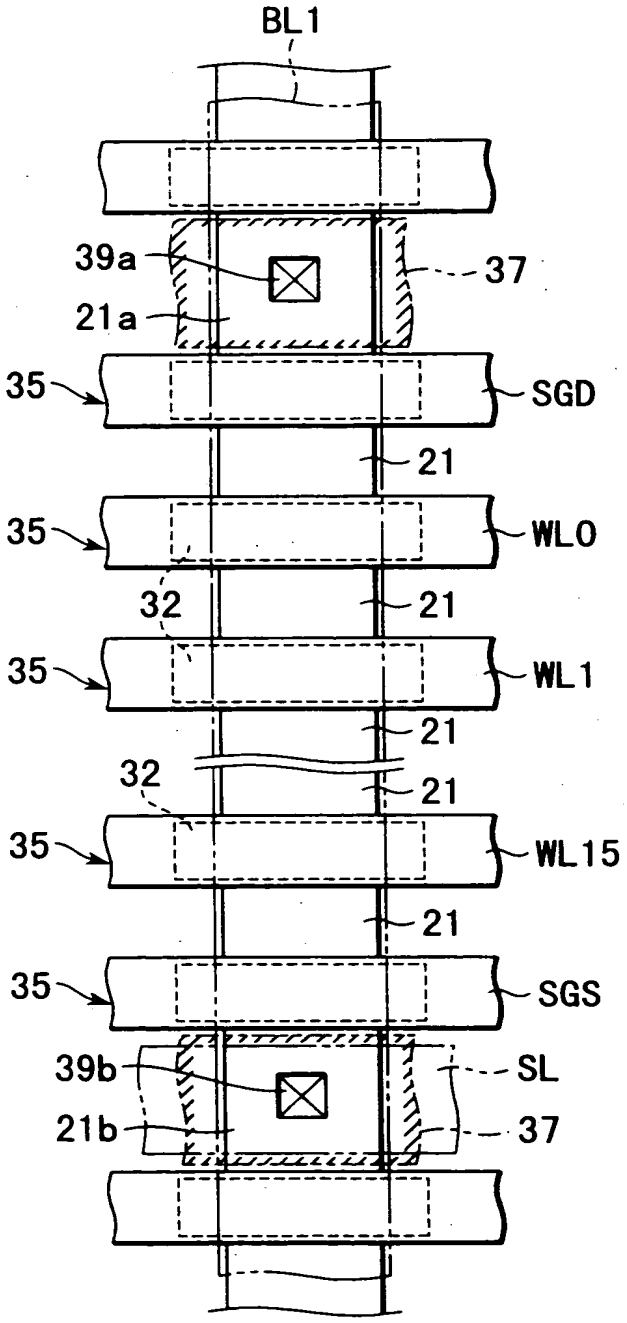

BL1
39a
37
21a
35
SGD
21
35
WL0
32
21
35
WL1
21
32
21
35
WL15
21
35
SGS
39b
SL
21b
37

FIG. 11

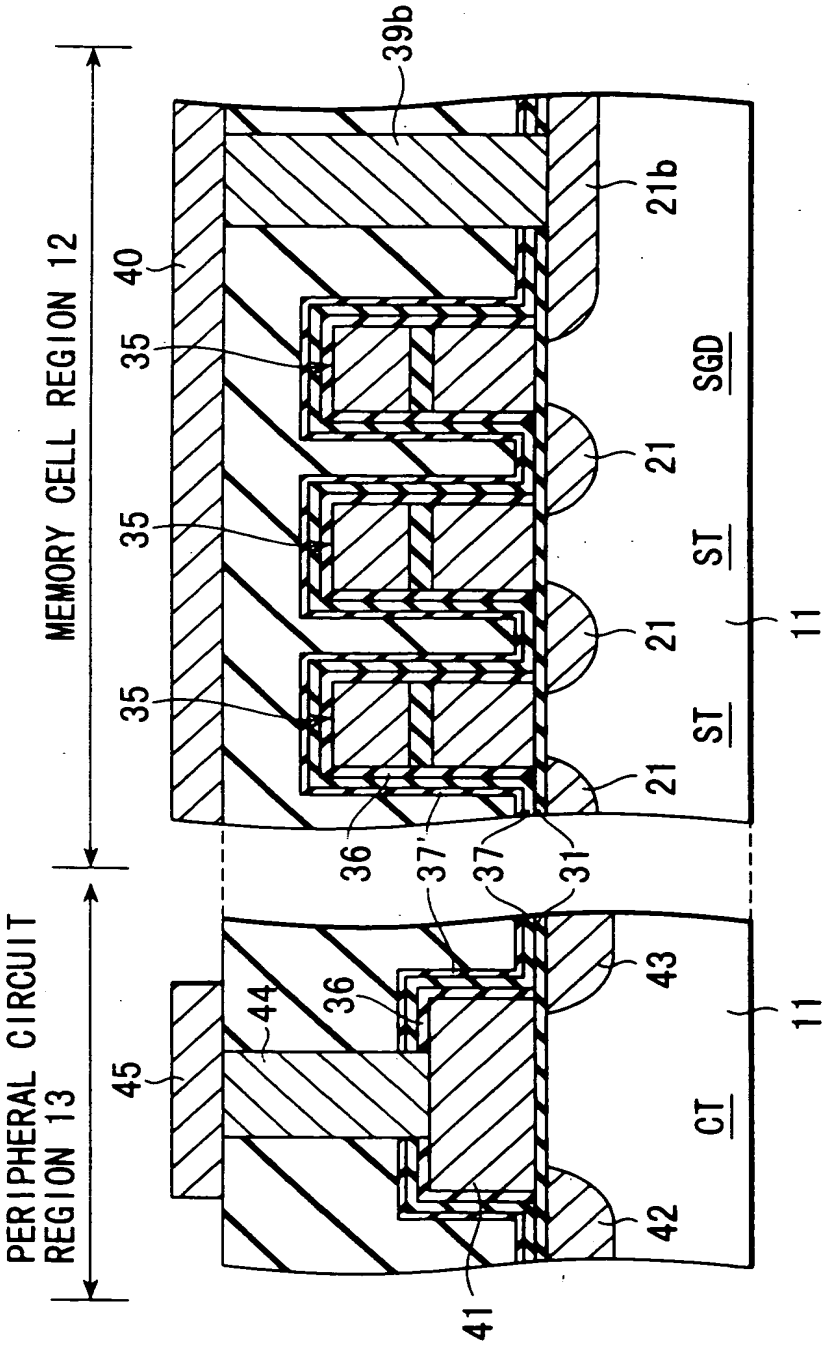

MEMORY CELL REGION 12
PERIPHERAL CIRCUIT REGION 13
39b
21b
40
35
35
35
21
21
21
SGD
ST
ST
11
11
36
37'
37
31
43
44
36
45
42
41
CT

FIG. 13

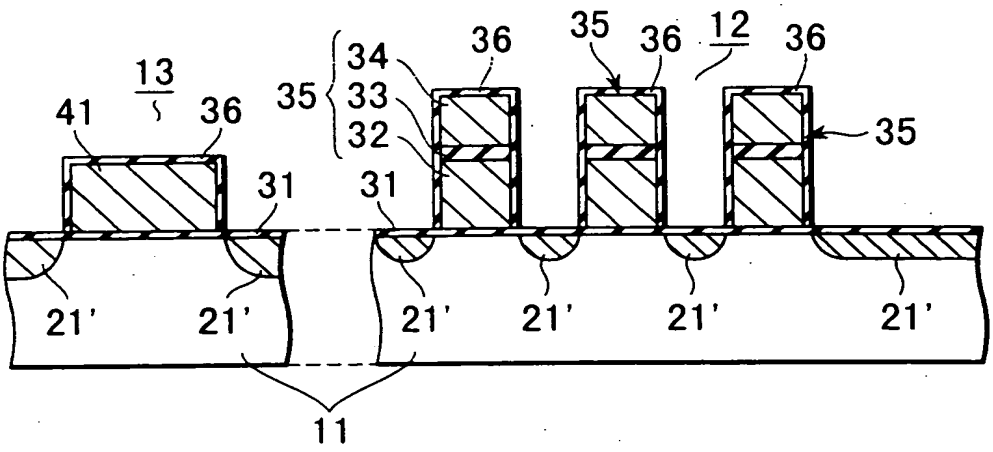


FIG. 14A

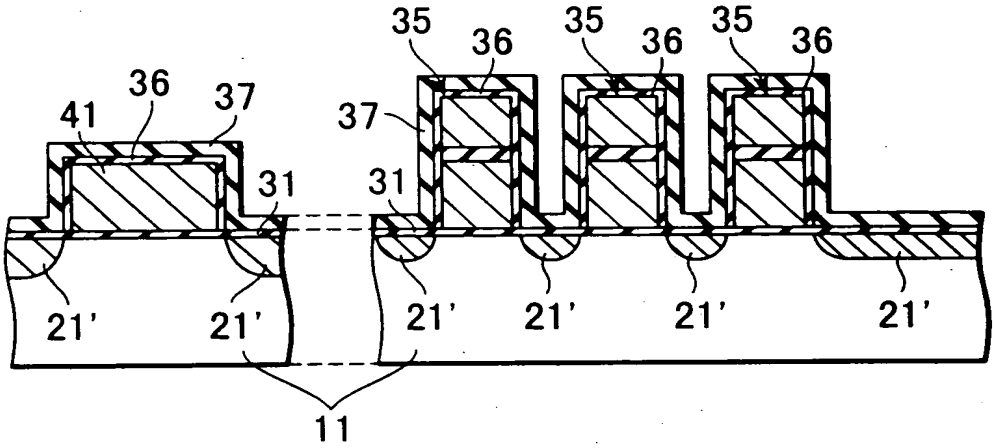


FIG. 14B

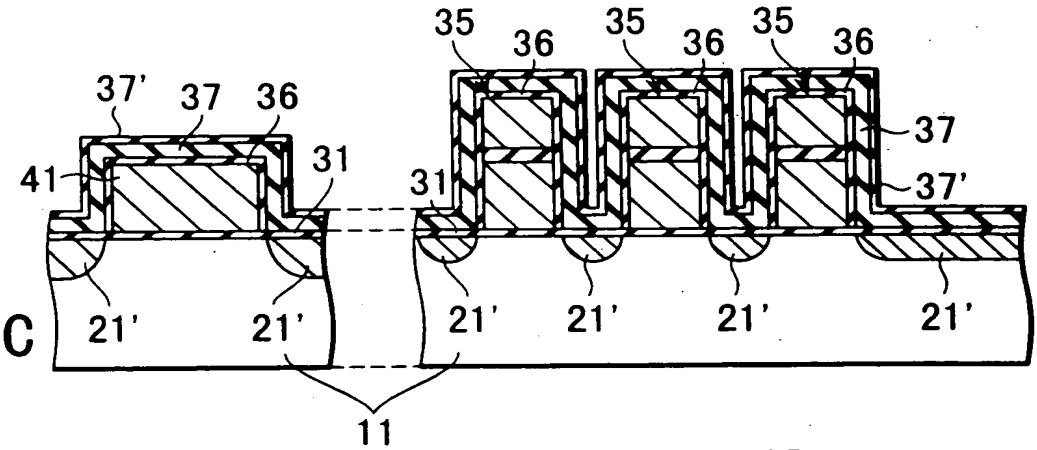


FIG. 14C

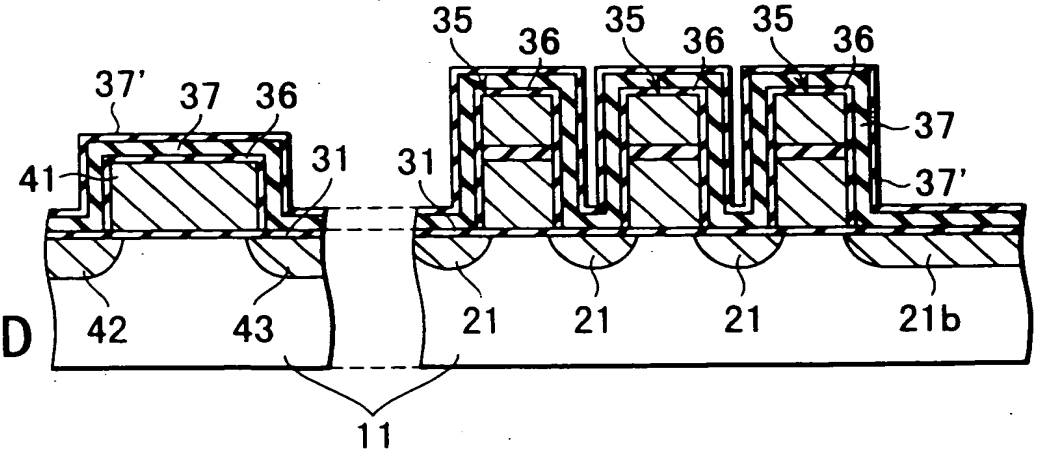
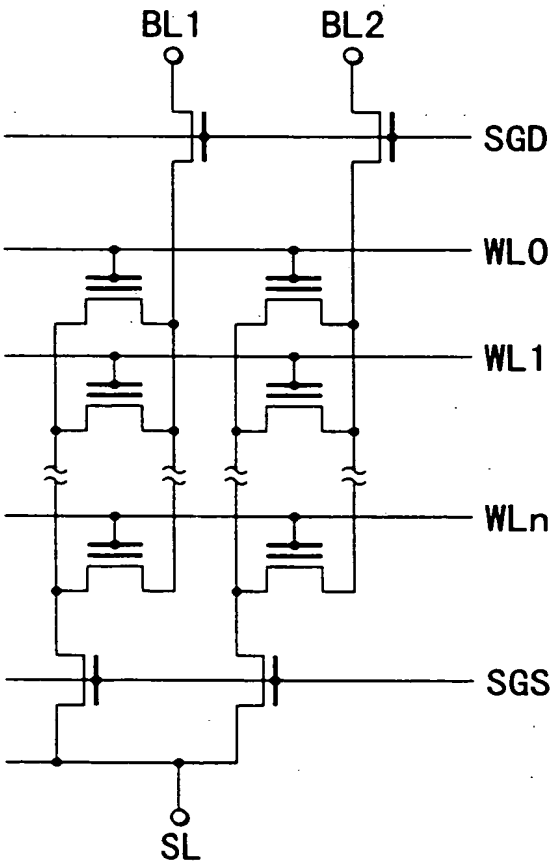


FIG. 14D

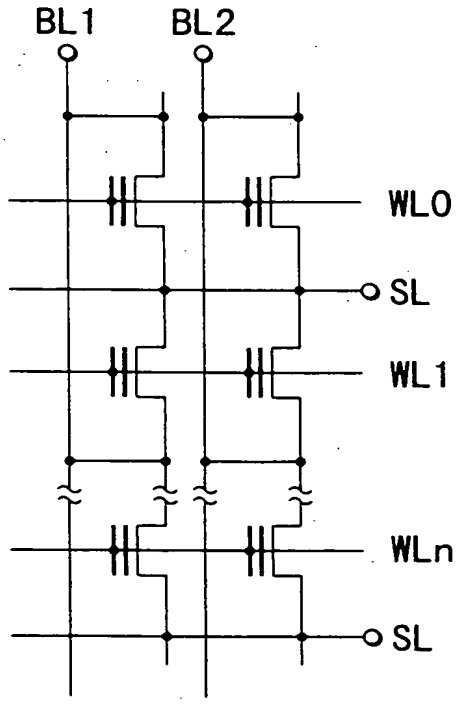
	CONCENTRATION OF HYDROGEN IN SiN FILM	CONCENTRATION OF HYDROGEN IN TUNNEL OXIDE FILM	dVg (ELECTRON AMOUNT TRAP)
NO SURFACE OXIDE FILM	4.0×10^{21} atom/cm^3	1	512mV
SURFACE OXIDE FILM FORMED	1.6×10^{21} atom/cm^3	0.2	398mV

FIG. 15



AND EEPROM

FIG. 16A



NOR EEPROM

FIG. 16B